DATA SHEET

BF909A; BF909AR
Dual-gate MOS-FETs

Preliminary specification
File under Discrete Semiconductors, SC07

1998 Mar 06

Philips
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FEATURES

- Specially designed for use at 5 V supply voltage
- High forward transfer admittance
- Short channel transistor with high forward transfer admittance to input capacitance ratio
- Low noise gain controlled amplifier up to 1 GHz
- Superior cross-modulation performance during AGC.

APPLICATIONS

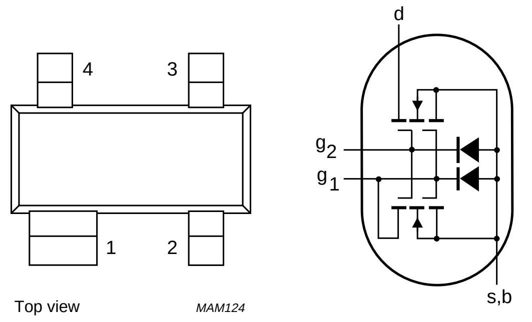
- VHF and UHF applications with 3 to 7 V supply voltage such as television tuners and professional communications equipment.

DESCRIPTION

Enhancement type field-effect transistor in a plastic microminiature SOT143B or SOT143R package. The transistor consists of an amplifier MOS-FET with source and substrate interconnected and an internal bias circuit to ensure good cross-modulation performance during AGC.

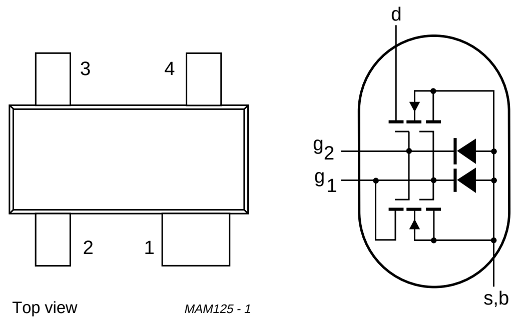
PINNING

PIN	SYMBOL	DESCRIPTION
1	s, b	source
2	d	drain
3	g_2	gate 2
4	g_1	gate 1



BF909A marking code: M33.

Fig.1 Simplified outline (SOT143B) and symbol.



BF909AR marking code: M34.

Fig.2 Simplified outline (SOT143R) and symbol.

QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V_{DS}	drain-source voltage		–	–	7	V
I_D	drain current		–	–	40	mA
P_{tot}	total power dissipation		–	–	200	mW
T_j	operating junction temperature		–	–	150	°C
$\|y_{fs}\|$	forward transfer admittance		36	43	50	mS
C_{ig1-s}	input capacitance at gate 1		–	3.6	4.3	pF
C_{rs}	reverse transfer capacitance	f = 1 MHz	–	35	50	fF
F	noise figure	f = 800 MHz	–	2	2.8	dB

CAUTION
This product is supplied in anti-static packing to prevent damage caused by electrostatic discharge during transport and handling. For further information, refer to Philips specs.: SNW-EQ-608, SNW-FQ-302A, and SNW-FQ-302B.

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{DS}	drain-source voltage		–	7	V
I_D	drain current		–	40	mA
I_{G1}	gate 1 current		–	±10	mA
I_{G2}	gate 2 current		–	±10	mA
P_{tot}	total power dissipation	see Fig.3			
	BF909A	$T_{amb} \leq 50$ °C; note 1	–	200	mW
	BF909AR	$T_{amb} \leq 40$ °C; note 1	–	200	mW
T_{stg}	storage temperature		–65	+150	°C
T_j	operating junction temperature		–	150	°C

Note

1. Device mounted on a printed-circuit board.

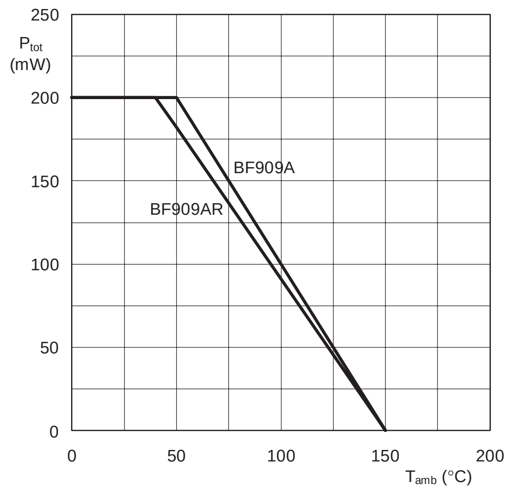


Fig.3 Power derating curves.

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j\text{-}a}$	thermal resistance from junction to ambient	note 1		
	BF909A		500	K/W
	BF909AR		550	K/W
$R_{th\ j\text{-}s}$	thermal resistance from junction to soldering point	note 2		
	BF909A	T_s = 92 °C	290	K/W
	BF909AR	T_s = 78 °C	360	K/W

Notes

1. Device mounted on a printed-circuit board.
2. T_s is the temperature at the soldering point of the source lead.

STATIC CHARACTERISTICS

T_j = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$V_{(BR)G1\text{-}SS}$	gate 1-source breakdown voltage	$V_{G2\text{-}S} = V_{DS} = 0$; $I_{G1\text{-}S}$ = 10 mA	6	15	V
$V_{(BR)G2\text{-}SS}$	gate 2-source breakdown voltage	$V_{G1\text{-}S} = V_{DS} = 0$; $I_{G2\text{-}S}$ = 10 mA	6	15	V
$V_{(F)S\text{-}G1}$	forward source-gate 1 voltage	$V_{G2\text{-}S} = V_{DS} = 0$; $I_{S\text{-}G1}$ = 10 mA	0.5	1.5	V
$V_{(F)S\text{-}G2}$	forward source-gate 2 voltage	$V_{G1\text{-}S} = V_{DS} = 0$; $I_{S\text{-}G2}$ = 10 mA	0.5	1.5	V
$V_{G1\text{-}S(th)}$	gate 1-source threshold voltage	$V_{G2\text{-}S}$ = 4 V; V_{DS} = 5 V; I_D = 20 μA	0.3	1	V
$V_{G2\text{-}S(th)}$	gate 2-source threshold voltage	$V_{G1\text{-}S} = V_{DS}$ = 5 V; I_D = 20 μA	0.3	1.2	V
I_{DSX}	drain-source current	$V_{G2\text{-}S}$ = 4 V; V_{DS} = 5 V; R_{G1} = 120 kΩ; note 1	12	20	mA
$I_{G1\text{-}SS}$	gate 1 cut-off current	$V_{G1\text{-}S}$ = 5 V; $V_{G2\text{-}S} = V_{DS} = 0$	–	50	nA
$I_{G2\text{-}SS}$	gate 2 cut-off current	$V_{G2\text{-}S}$ = 5 V; $V_{G1\text{-}S} = V_{DS} = 0$	–	50	nA

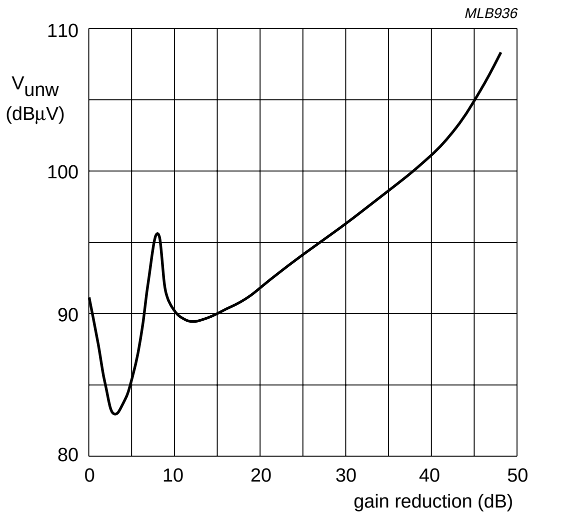
Note

1. R_{G1} connects gate 1 to V_{GG} = 5 V; see Fig.18.

DYNAMIC CHARACTERISTICS

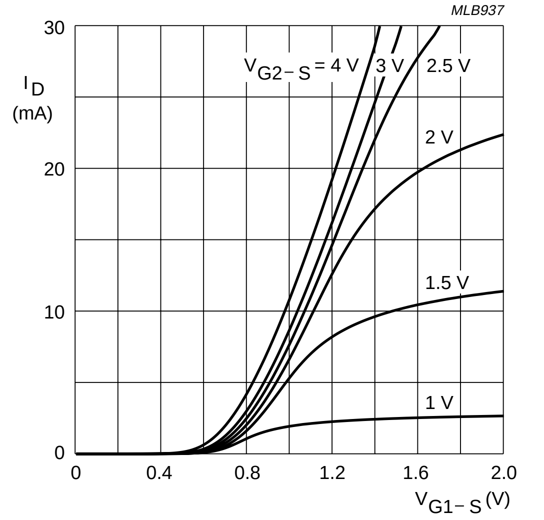
Common source; T_{amb} = 25 °C; V_{DS} = 5 V; $V_{G2\text{-}S}$ = 4 V; I_D = 15 mA; unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$\lvert y_{fs} \rvert$	forward transfer admittance	pulsed; T_j = 25 °C	36	43	50	mS
$C_{ig1\text{-}s}$	input capacitance at gate 1	f = 1 MHz	–	3.6	4.3	pF
$C_{ig2\text{-}s}$	input capacitance at gate 2	f = 1 MHz	–	2.3	3	pF
C_{os}	drain-source capacitance	f = 1 MHz	–	2.4	3	pF
C_{rs}	reverse transfer capacitance	f = 1 MHz	–	35	50	fF
F	noise figure	f = 800 MHz; $G_S = G_{Sopt}$; $B_S = B_{Sopt}$	–	2	2.8	dB



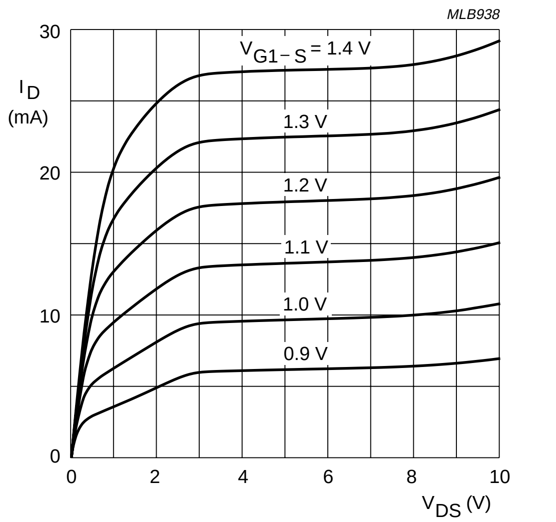
V_{DS} = 5 V; V_{GG} = 5 V; f_w = 50 MHz.
f_{unw} = 60 MHz; T_{amb} = 25 °C; R_{G1} = 120 kΩ.

Fig.4 Unwanted voltage for 1% cross-modulation as a function of gain reduction; typical values; see Fig.18.



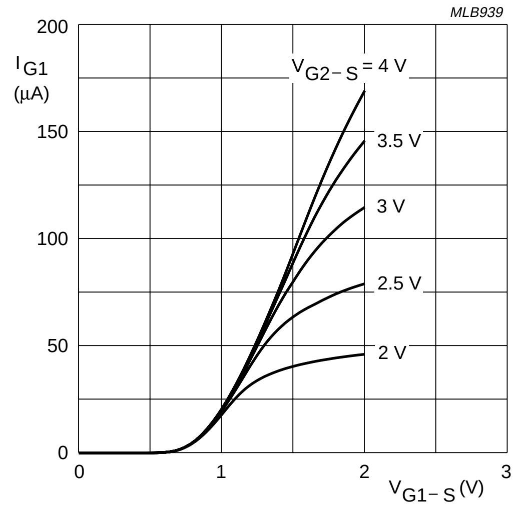
V_{DS} = 5 V.
T_j = 25 °C.

Fig.5 Transfer characteristics; typical values.



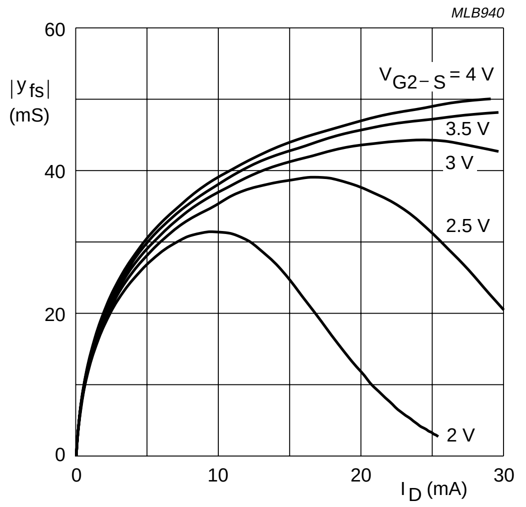
V_{DS} = 5 V.
$V_{G2\text{-}S}$ = 4 V.
T_j = 25 °C.

Fig.6 Output characteristics; typical values.



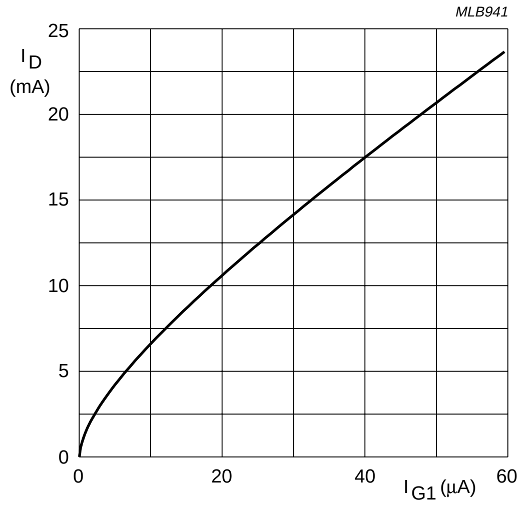
V_{DS} = 5 V.
T_j = 25 °C.

Fig.7 Gate 1 current as a function of gate 1 voltage; typical values.



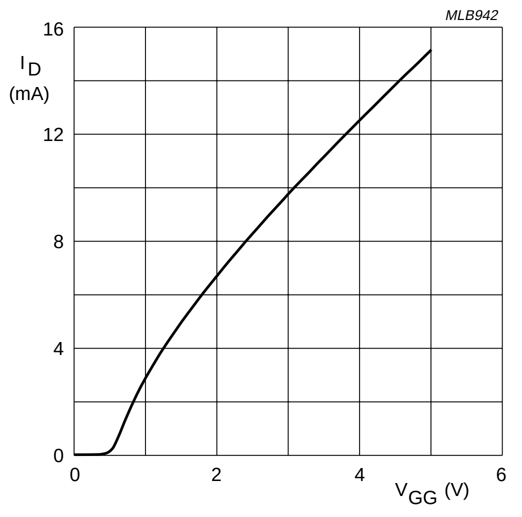
V_{DS} = 5 V.
T_j = 25 °C.

Fig.8 Forward transfer admittance as a function of drain current; typical values.



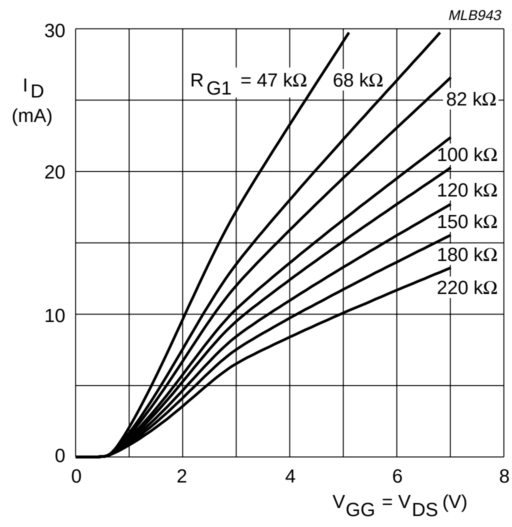
V_{DS} = 5 V; V_{G2-S} = 4 V.
T_j = 25 °C.

Fig.9 Drain current as a function of gate 1 current; typical values.



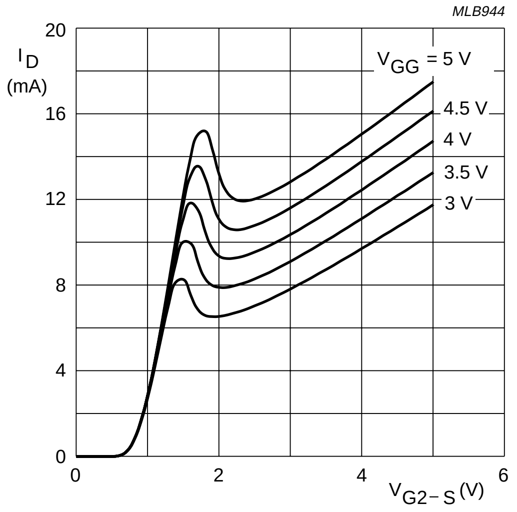
V_{DS} = 5 V; V_{G2-S} = 4 V.
R_{G1} = 120 kΩ (connected to V_{GG}); T_j = 25 °C.

Fig.10 Drain current as a function of gate 1 supply voltage (= V_{GG}); typical values; see Fig.18.



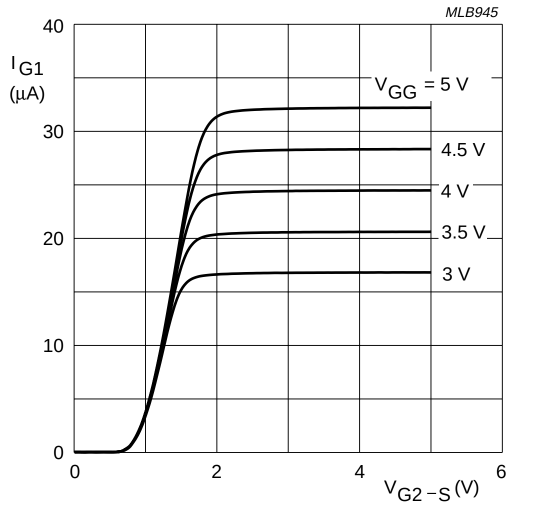
V_{G2-S} = 4 V.
R_{G1} connected to V_{GG}; T_j = 25 °C.

Fig.11 Drain current as a function of gate 1 (= V_{GG}) and drain supply voltage; typical values; see Fig.18.



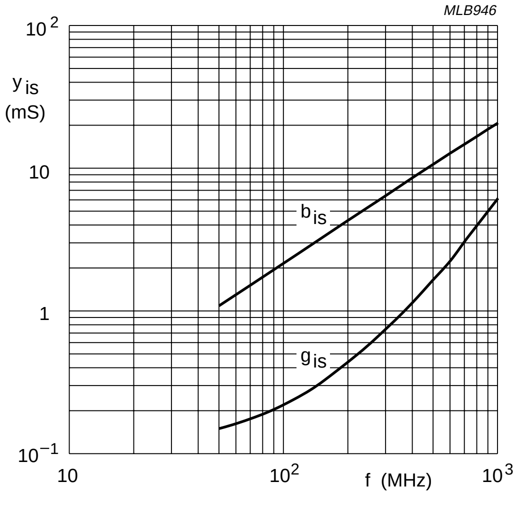
V_{DS} = 5 V; T_j = 25 °C.
R_{G1} = 120 kΩ (connected to V_{GG}).

Fig.12 Drain current as a function of gate 2 voltage; typical values; see Fig.18.



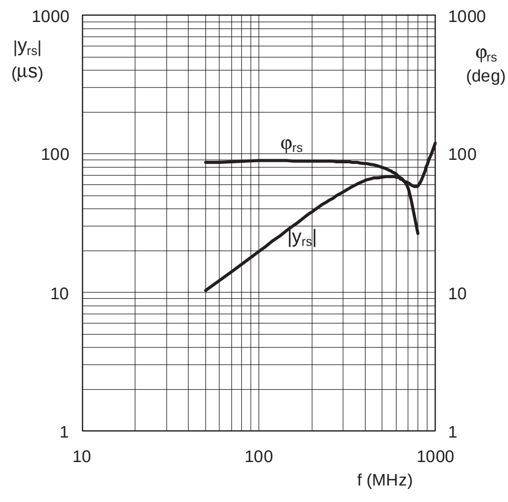
V_{DS} = 5 V; T_j = 25 °C.
R_{G1} = 120 kΩ (connected to V_{GG}).

Fig.13 Gate 1 current as a function of gate 2 voltage; typical values; see Fig.18.



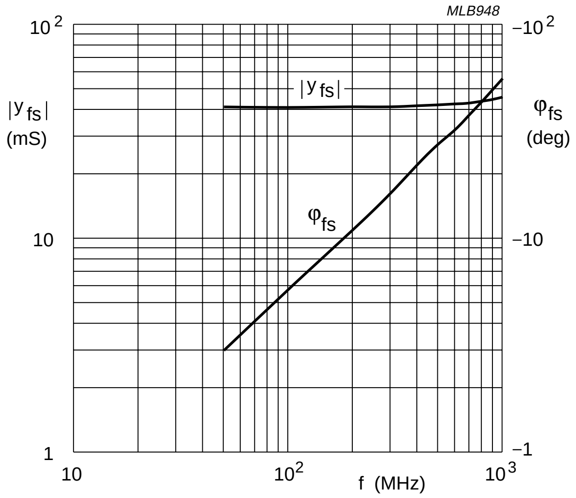
V_{DS} = 5 V; V_{G2} = 4 V.
I_D = 15 mA; T_{amb} = 25 °C.

Fig.14 Input admittance as a function of frequency; typical values.



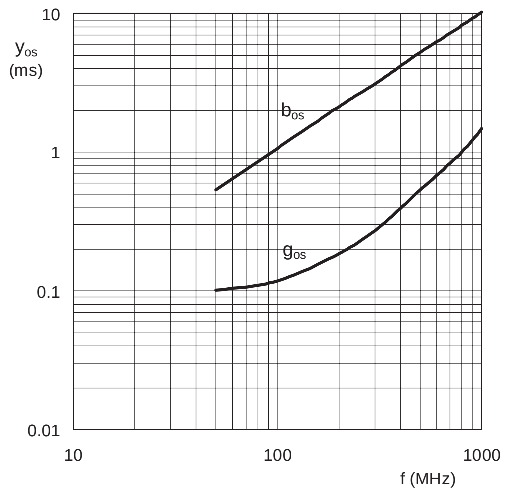
V_{DS} = 5 V; V_{G2} = 4 V.
I_D = 15 mA; T_{amb} = 25 °C.

Fig.15 Reverse transfer admittance and phase as a function of frequency; typical values.



V_{DS} = 5 V; V_{G2} = 4 V.
I_D = 15 mA; T_{amb} = 25 °C.

Fig.16 Forward transfer admittance and phase as a function of frequency; typical values.



V_{DS} = 5 V; V_{G2} = 4 V.
I_D = 15 mA; T_{amb} = 25 °C.

Fig.17 Output admittance as a function of frequency; typical values.

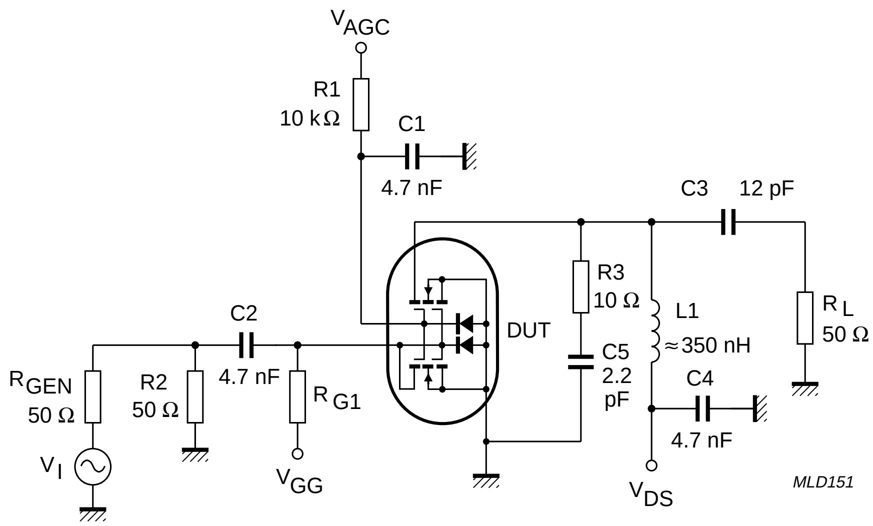


Fig.18 Cross-modulation test set-up.

Table 1 Scattering parameters: T_{amb} = 25 °C; V_{DS} = 5 V; V_{G2-S} = 4 V; I_D = 15 mA

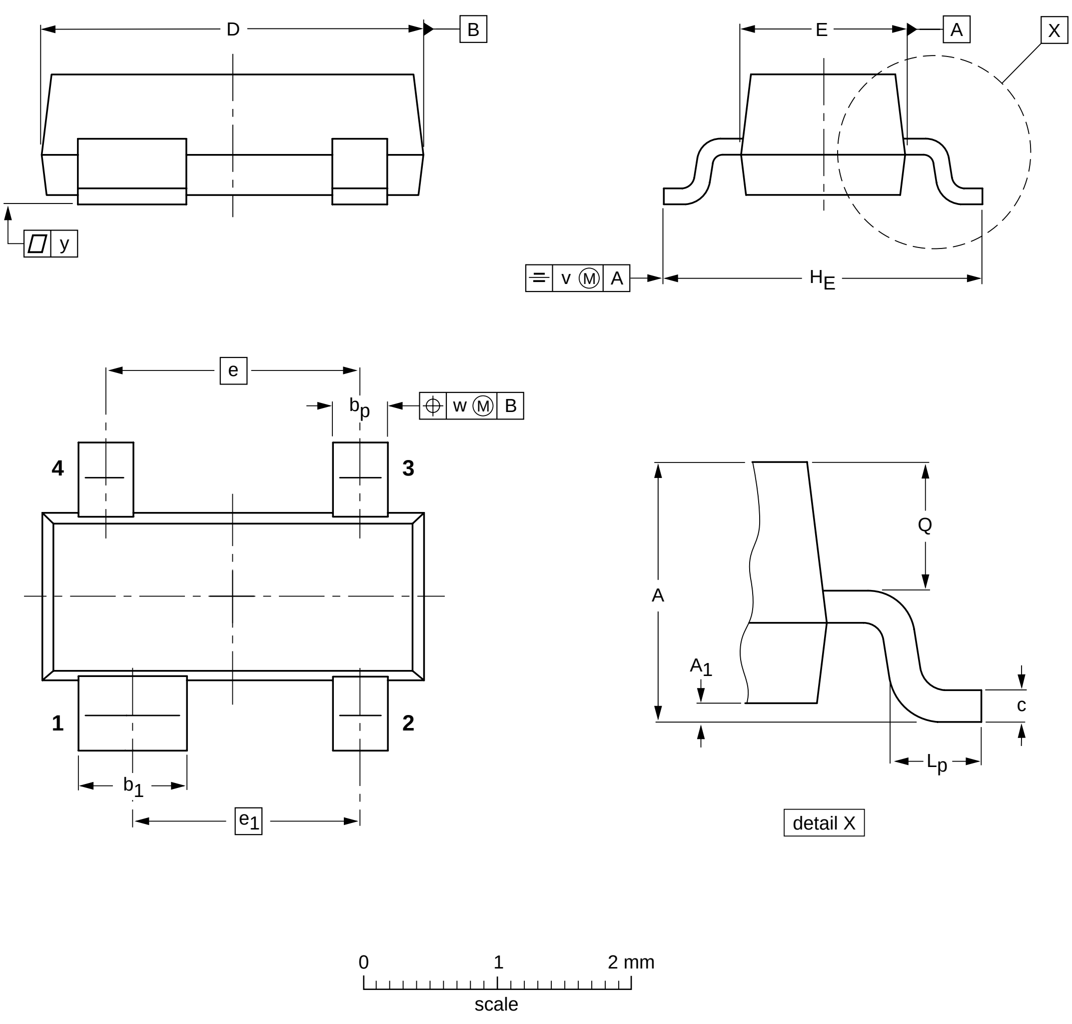
f (MHz)	s_{11}		s_{21}		s_{12}		s_{22}	
	MAGNITUDE (ratio)	ANGLE (deg)	MAGNITUDE (ratio)	ANGLE (deg)	MAGNITUDE (ratio)	ANGLE (deg)	MAGNITUDE (ratio)	ANGLE (deg)
50	0.988	–5.9	4.258	172.8	0.001	89.1	0.990	–3.2
100	0.982	–11.9	4.219	165.4	0.002	81.9	0.998	–6.4
200	0.964	–23.4	4.090	151.7	0.004	73.9	0.979	–12.6
300	0.939	–34.3	3.899	138.4	0.005	66.8	0.969	–18.6
400	0.911	–44.7	3.708	125.9	0.005	61.7	0.956	–24.4
500	0.883	–54.2	3.467	114.2	0.005	60.5	0.944	–29.9
600	0.853	–62.9	3.246	103.3	0.005	63.3	0.934	–35.1
700	0.828	–70.9	3.036	92.7	0.004	72.4	0.924	–40.1
800	0.805	–78.3	2.843	82.5	0.004	97.9	0.916	–45.1
900	0.777	–85.4	2.634	72.6	0.005	121.3	0.906	–50.0
1000	0.749	–91.8	2.450	63.2	0.006	138.7	0.890	–54.9

Table 2 Noise data: T_{amb} = 25 °C; V_{DS} = 5 V; V_{G2-S} = 4 V; I_D = 15 mA

f (MHz)	F_{min} (dB)	Γ_{opt}		r_n
		(ratio)	(deg)	
800	2.00	0.603	67.71	0.581

PACKAGE OUTLINES

Plastic surface mounted package; 4 leads **SOT143B**



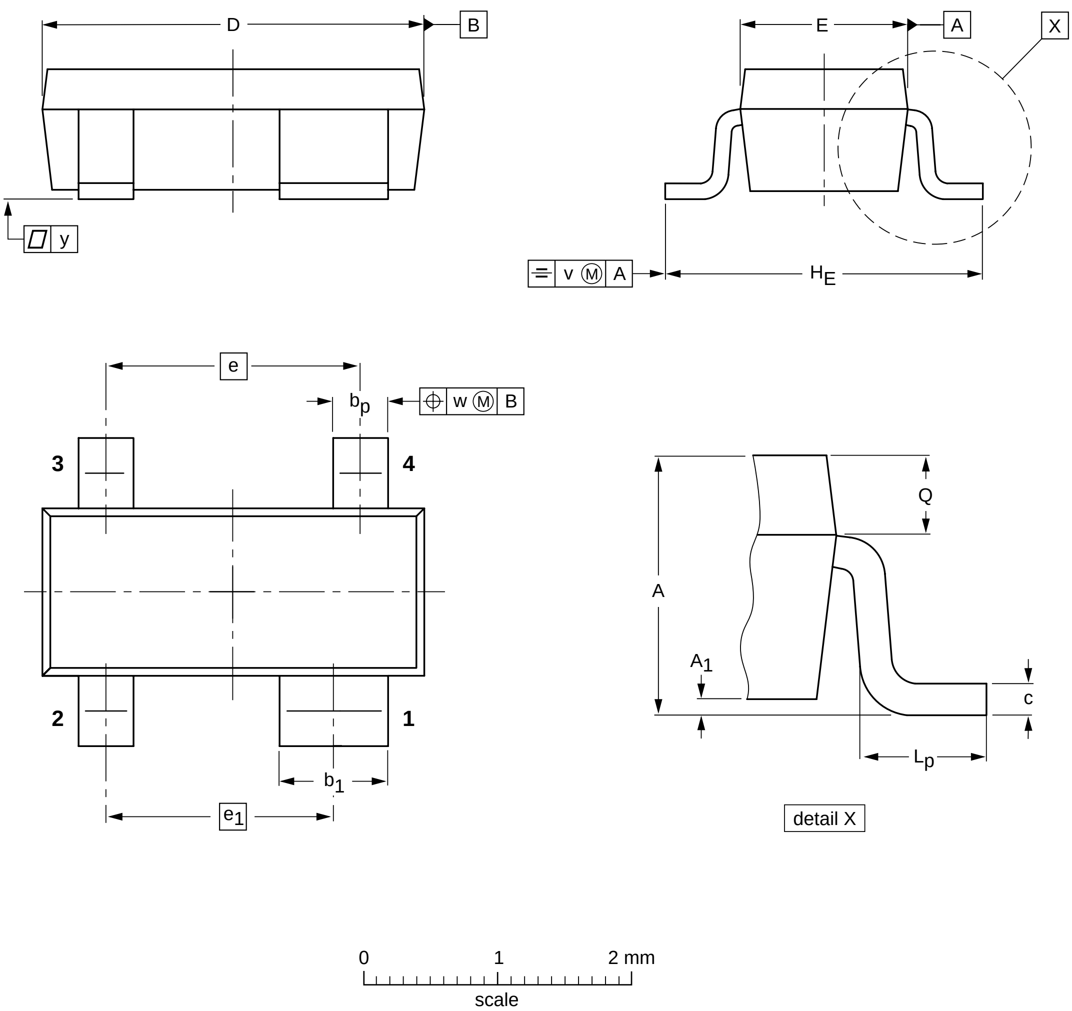
DIMENSIONS (mm are the original dimensions)

UNIT	A	A_1 max	b_p	b_1	c	D	E	e	e_1	H_E	L_p	Q	v	w	y
mm	1.1 0.9	0.1	0.48 0.38	0.88 0.78	0.15 0.09	3.0 2.8	1.4 1.2	1.9	1.7	2.5 2.1	0.45 0.15	0.55 0.45	0.2	0.1	0.1

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT143B						97-02-28

PACKAGE OUTLINES

Plastic surface mounted package; reverse pinning; 4 leads **SOT143R**



DIMENSIONS (mm are the original dimensions)

UNIT	A	A_1 max	b_p	b_1	c	D	E	e	e_1	H_E	L_p	Q	v	w	y
mm	1.1 0.9	0.1	0.48 0.38	0.88 0.78	0.15 0.09	3.0 2.8	1.4 1.2	1.9	1.7	2.5 2.1	0.55 0.25	0.45 0.25	0.2	0.1	0.1

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT143R						97-03-10

DEFINITIONS

Data Sheet Status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Limiting values	
Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
Application information	
Where application information is given, it is advisory and does not form part of the specification.	

LIFE SUPPORT APPLICATIONS

These products are not designed for use in life support appliances, devices, or systems where malfunction of these products can reasonably be expected to result in personal injury. Philips customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Philips for any damages resulting from such improper use or sale.

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